Abstract

An aluminum nitride junction body useful as an electrostatic chuck for holding a semiconductor wafer in an apparatus for producing a semiconductor, comprising aluminum nitride sintered plates joined together via a sintered metal layer. When used in the above application, the junction structure works to uniformly adsorb the semiconductor wafer. The aluminum nitride junction body is obtained by joining aluminum nitride sintered plates 1-a and 1-b together having a sintered metal layer 2 of tungsten or molybdenum of a thickness of 15 to 100 μm formed on at least a portion of the junction surface thereof, the sintered metal layer having a sheet resistivity of not larger than 1 Ω/□ and warping by not more than 100 μ/100 mm.